

Docket No.: 740756-2688
Serial No.: 10/735,627

REMARKS

The Office Action of August 28, 2006 was received and reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application.

Reconsideration and withdrawal of the currently pending rejections are requested for the reasons advanced in detail below.

Claims 1-36 were pending prior to the instant amendment for consideration, of which claims 1, 2, 4, 5 and 7 are independent, and claims 26-36 are withdrawn. By this amendment, claims 1, 2, 4, 5, and 7 are amended, and new claims 37-41 are added to recite features of the present invention to which Applicants are entitled. Consequently, claims 1-41 are currently pending for consideration in the instant application.

Referring now to the detailed Office Action, claims 1, 16 and 21 stand rejected under 35 U.S.C. §103(a) as being anticipated by Nakamura et al. (U.S. Patent No. 6,887,724 – hereafter Nakamura), in view of Yamazaki et al. Further, claims 2-6, 11-14, 17-19 and 22-24 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Nakamura in view of Nishimura et al. (U.S. Patent No. 6,462,802 – hereafter Nishimura). Finally, claims 7-10, 15, 20 and 25 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Nakamura and Nishimura and further in view of Fujikawa et al. (U.S. Patent No. 6,836,140 – hereafter Fujikawa). These rejections are respectfully traversed at least for the reasons provided below.

The presently claimed invention, as recited in amended independent claims 1, 2, 4, 5 and 7, includes, among other features, a semiconductor film which is formed to have a low concentration impurity region overlapping the gate electrode (e.g., element 208), and a step of measuring resistance of the low concentration impurity region of the TEG (Test Element Group). An object of the present invention is to form a TEG for measuring an impurity concentration of a gate-overlapped region, as disclosed on page 4, lines 8-11, (i.e., paragraph [0014] of the substitute specification submitted July 27, 2004).

Claims 1, 16 and 21 are rejected under 35 U.S.C. § 103(a) as being obvious over Nakamura et al. (6,887,724) in view of Yamazaki et al. (2003/0207502). The Examiner relies on Yamazaki et al. for curing the deficiency of Nakamura et al., since Yamazaki et al. is alleged to disclose a low concentration impurity region overlapping the gate electrode.

Claims 2-6, 11-14, 17-19 and 22-24 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Nakamura et al. in view of Yamazaki et al. further in view of Nishimura et

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al. (6,462,802). The Examiner is relying on Nishimura et al. for curing the deficiency of Nakamura et al., since Nishimura et al. is alleged to disclose a gate electrode that is laminated with a first conductive film and a second conductive film. Also, the Examiner is relying on Yamazaki et al. for curing the deficiency of Nakamura et al., since Yamazaki et al. is alleged to disclose a low concentration impurity region overlapping the gate electrode.

Claims 7-10, 15, 20 and 25 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Nakamura et al. in view of Yamazaki et al. further in view of Nishimura et al. and Fujikawa et al. (6,836,140). The Examiner is relying on Nishimura et al. for curing the deficiency of Nakamura et al., since Nishimura et al. is alleged to disclose a gate electrode that is laminated with a first conductive film and a second conductive film. Also, the Examiner is relying on Yamazaki et al. for curing the deficiency of Nakamura et al., since Yamazaki et al. is alleged to disclose a low concentration impurity region overlapping the gate electrode and relying on Fujikawa et al. since Fujikawa et al. disclose a plurality of first to third TEGS.

Applicants contend that the present invention is patentably distinguishable over the cited references for, at least, the reasons advanced in detail below. Specifically, with respect to claims 2, 5 and 7, the present invention discloses a feature that "a side edge portion of the semiconductor film is provided between the edge of the first conductive film and the edge of the second conductive film" as shown in the attached sheet of FIG.1(iii).

On the other hand, it appears that cited references fail to disclose this feature. The Examiner is asserting that Nishimura et al. disclose the feature in FIG.1; col. 12, line 65 thru col. 13, line 13. However, Applicants could not find the feature in Nishimura et al. Therefore, Applicants contend that, even when the cited references are combined, the present invention can not be obtained. In view of the above, Applicants believe the rejections of claims 2, 5 and 7, as well as the claims depending therefrom, are overcome.

With respect to claims 1 and 4, claims 1 and 4 are amended so as to add "a gate electrode which is formed to have a first conductive film ...and a second conductive film..." and "an edge of the first conductive film extends beyond an edge of the second conductive film, and a side edge portion of the semiconductor film is provided between the edge of the first conductive film and the edge of the second conductive film" in order to distinguish the present invention from cited references, as shown in the attached sheet. Applicants contend that amended claims 1 and 4 are distinguishable over cited references. In view of the above,

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the rejections of claims 1 and 4, as well as the claims depending therefrom, should be overcome.

Claims 1 and 4 are also amended to add "etching is performed simultaneously on the gate electrode of the TEG and the gate electrode of the TFT" or "the gate electrode with the taper is formed by taper etching, which is performed simultaneously on the gate electrode of the TEG and the gate electrode of the TFT" for variation between claims 1 and 2, and claims 4 and 5.

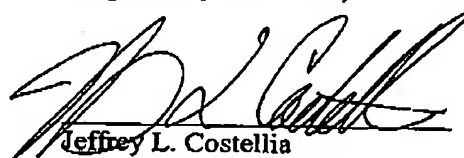
Further, claims 2, 5 and 7 are slightly amended to clarify the claim language.

Applicants have also added new claims 37-41 in order to recite additional features to which Applicants are entitled.

In view of the foregoing, it is respectfully requested that the rejections of record be reconsidered and withdrawn by the Examiner, that claims 1-41 be allowed and that the application be passed to issue. If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

The Commissioner is authorized to charge any overage or shortage of fees connected with filing of this Amendment to Deposit Account No. 19-2380.

Respectfully submitted,



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